

LISTINGS OF THE CLAIMS:

Please **cancel** claims 27, 31, 32, 37, 49 and 50 without prejudice.

1-32. (Cancelled)

33. (Previously presented) A method for manufacturing a liquid crystal display (LCD), comprising the steps of:

forming a color filter layer on a substrate;
forming a conductive layer on the color filter layer;
forming an insulating layer on the conductive layer;
forming a photoresist layer on the insulating layer; and
 patterning the insulating layer and the photoresist layer to form a protrusion and a spacer taller than the protrusion.

34. (Previously presented) The method of claim 33, wherein the step of patterning the insulating layer and the photoresist layer comprising steps of:

preparing a mask having an opaque area, a semitransparent area and a transparent area on predetermined areas thereof;
exposing the photoresist layer to a light beam through the mask;
developing the photoresist layer to expose portions of the insulating layer; and
etching the exposed portions of the insulating layer.

35. (Previously presented) The method of claim 34, wherein the insulating layer contains silicon.

36. (Cancelled)

37. (Cancelled)

38. (Previously presented) The method of claim 33, further comprising a step of forming a black matrix layer on the substrate, wherein the spacer overlaps the black matrix layer.

39. (Previously presented) A method for manufacturing a liquid crystal display (LCD), comprising steps of:

forming a black matrix layer on a first substrate, the black matrix layer comprising a first black matrix pattern surrounding a pixel region and a second black matrix pattern formed within the pixel region;

forming a color filter layer on the black matrix layer;

forming a conductive layer on the color filter layer; and

forming a protrusion on a portion of the conductive layer corresponding to the second black matrix pattern, the protrusion having a height to maintain a predetermined gap between the first substrate and a second substrate facing the first substrate.

40. (Previously presented) The method of claim 39, wherein the height of the protrusion ranges between 3.0 μm and 4.5 μm .

41. (Previously presented) The method of claim 39, wherein the protrusion is pillar-shaped.

42. (Previously presented) The method of claim 41, wherein a top surface and a bottom surface of the protrusion have a circular or rectangular shape or a rectangular shape with curved edges.

43. (Previously presented) The method of claim 39, wherein the protrusion is formed of a photosensitive material, positive or negative photoresist or an insulating material containing silicon.

44. (Previously presented) The method of claim 39, wherein the pixel region is divided into a plurality of sub-regions and the protrusion is formed within each sub-region.

45. (Previously presented) The method of claim 44, wherein the protrusion is formed at the center of each sub-region.
46. (Previously presented) The method of claim 39, wherein the protrusion is in contact with a pixel electrode of the second substrate to maintain the predetermined gap between the first substrate and the second substrate.
47. (Previously presented) The method of claim 33, wherein the spacer comprises the insulating layer and the photoresist layer.
48. (Previously presented) The method of claim 47, wherein the protrusion comprises the insulating layer.
49. (Cancelled)
50. (Canceled)